

## SOT-323 Plastic-Encapsulate DIODE

**BAW56W** SWITCHING DIODE

### FEATURES

Power dissipation

$P_D$ : 200 mW ( $T_{amb}=25^\circ\text{C}$ )

Collector current

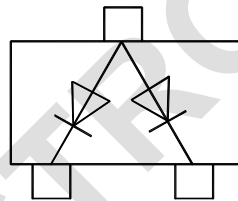
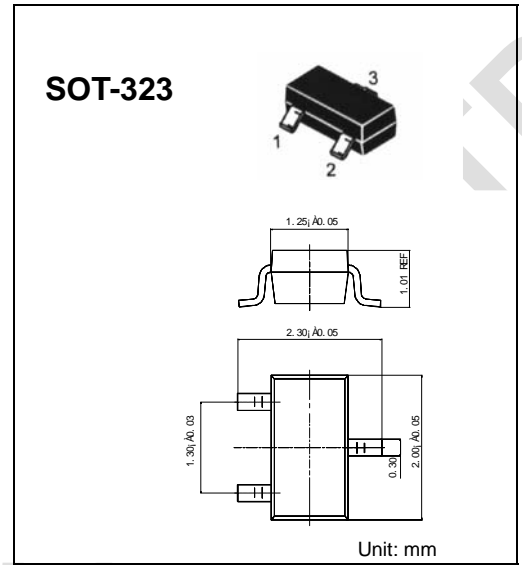
$I_O$ : 150 mA

Collector-base voltage

$V_R$ : 75 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^\circ\text{C}$  to  $+150^\circ\text{C}$



Marking: KJC

### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu\text{A}$	75		V
Reverse voltage leakage current	$I_R$	$V_R=75\text{V}$		2.5	$\mu\text{A}$
Forward voltage	$V_F$	$I_F=1\text{mA}$ $I_F=10\text{mA}$ $I_F=50\text{mA}$ $I_F=150\text{mA}$		715 855 1000 1250	mV
Diode capacitance	$C_D$	$V_R=0\text{V}, f=1\text{MHz}$		2	pF
Reveres recovery time	$t_{rr}$	$I_F=I_R=10\text{mA}$ $I_{rr}=0.1 \times I_R$		4	nS